

Features

- Frequency: 34GHz~36GHz
- Power Gain: 15.5dB
- Psat: 41.5dBm
- P.A.E: 20%
- +22V @ 3A (Quiescent)
- Chip Size: 5.05mm×4.76mm×0.10mm

Electrical Specification (TA=+25°C, Vd=+22V, Vg=-1.8V)

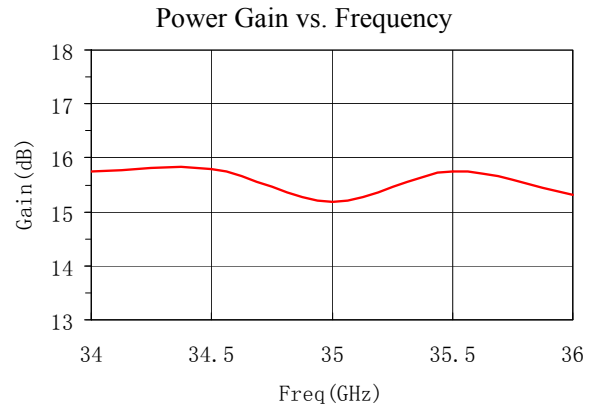
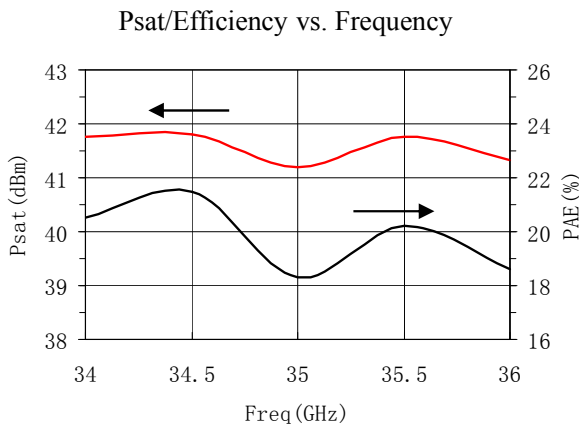
Parameter	Min.	Typ.	Max	Unit
Frequency	34-36			GHz
Psat		41.5		dBm
Power Gain		15.5		dB
P.A.E		20		%
Dynamic Operating Current	3			A

Note: 1) All chips have been 100% DC tested.
 2) Test condition: Vd=+22V, Vg=-1.8V, P_{in}=26dBm, pulse width 100μs, duty cycle 2%.

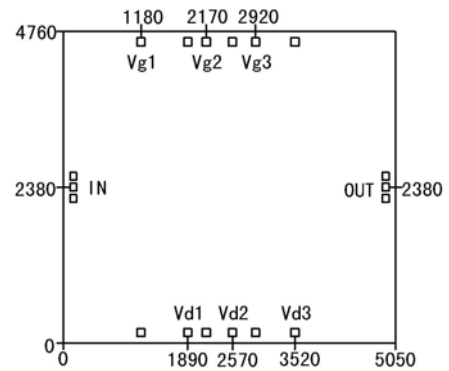
Limited Rating Values

Vds	+24V
Vgs	-6V
Input CW Power	+30dBm
Channel Temperature	+175°C
Storage Temperature	-65°C ~ +150°C

Typical Testing Curves

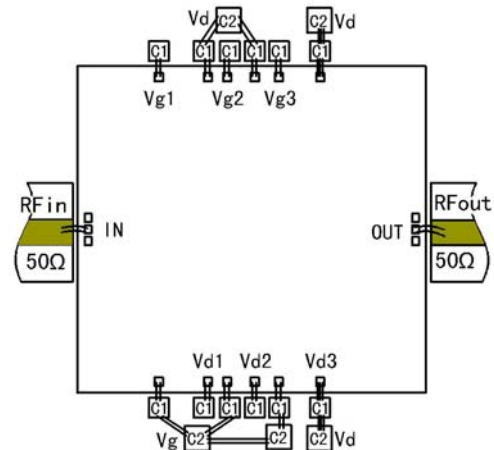


Dimension and Outline



Note: The unit is μm.
 Input and output pad dimension: 100×120μm².
 Bias pad dimension: 120×120μm²

Assembly Diagram



Note: External capacitor C1:100pF, C2:1000pF.

Attention

- 1) Two bonding wires are needed for input and output (diameter: 25μm). Bonding wires shall not be longer than 500μm.
- 2) Bonding with 80/20 Au/Sn. Temperature should be lower than 300°C and time should be less than 30 seconds.
- 3) Blocking capacitors in Input/Output are already integrated.